

ABSTRACT OF THE DISCLOSURE

Method for increasing the structure density and/or the storage capacitance of structures to be introduced into a semiconductor wafer, the semiconductor wafer having a marking prescribing a breaking direction and the structures being imaged onto the semiconductor wafer by means of an exposure device and a mask, whose mask layout prescribes the structures. The semiconductor wafer is rotated by 45 degrees in its plane with regard to the mask layout prior to the imaging of the structures and provided with a marking prescribing a new breaking direction parallel to a <100> crystal orientation. The further process steps take place unchanged with respect to nonrotated semiconductor wafers.

Document #: 1262114 v.1